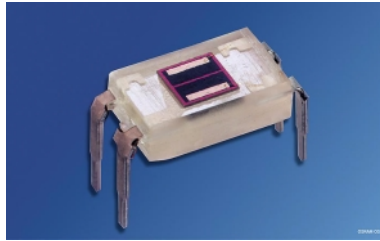


# Silizium-Differential-Fotodiode Silicon Differential Photodiode

## BPX 48 BPX 48 F



BPX 48



BPX 48 F

### Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 400 nm bis 1100 nm (BPX 48) und bei 920 nm (BPX 48 F)
- Hohe Fotoempfindlichkeit
- DIL-Plastikbauform mit hoher Packungsdichte
- Doppeldiode mit extrem hoher Gleichmäßigkeit

### Anwendungen

- Nachlaufsteuerung
- Kantenführungen
- Weg- bzw. Winkelabtastungen
- Industrieelektronik
- „Messen/Steuern/Regeln“

### Features

- Especially suitable for applications from 400 nm to 1100 nm (BPX 48) and of 920 nm (BPX 48 F)
- High photosensitivity
- DIL plastic package with high packing density
- Double diode with extremely high homogeneousness

### Application

- Follow-up control
- Edge control
- Path and angle scanning
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code
BPX 48	Q62702-P17-S1
BPX 48 F	Q62702-P305

**Grenzwerte**
**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 80	°C
Löttemperatur (Lötstelle 2 mm vom Gehäuse entfernt bei Lötzeit $t \leq 3$ s) Soldering temperature in 2 mm distance from case bottom ( $t \leq 3$ s)	$T_S$	230	°C
Sperrspannung Reverse voltage	$V_R$	10	V
Verlustleistung, $T_A = 25$ °C Total power dissipation	$P_{tot}$	50	mW

**Kennwerte** ( $T_A = 25$  °C) für jede Einzeldiode

**Characteristics** ( $T_A = 25$  °C) per single diode system

Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		BPX 48	BPX 48 F	
Fotostrom Photocurrent $V_R = 5$ V, Normlicht/standard light A, $T = 2856$ K, $E_V = 1000$ lx $V_R = 5$ V, $\lambda = 950$ nm, $E_e = 0.5$ mW/cm <sup>2</sup>	$I_P$  $I_P$	24 ( $\geq 15$ ) -	- 7.5 ( $\geq 4.0$ )	$\mu$ A  $\mu$ A
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\ max}$	900	920	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von $S_{max}$ Spectral range of sensitivity $S = 10\%$ of $S_{max}$	$\lambda$	400 ... 1150	750 ... 1150	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	$A$	1.54	1.54	mm <sup>2</sup>
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$  $L \times W$	$0.7 \times 2.2$	$0.7 \times 2.2$	mm $\times$ mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	$H$	0.5	0.5	mm

**Kennwerte** ( $T_A = 25\text{ °C}$ ) für jede Einzeldiode  
**Characteristics** ( $T_A = 25\text{ °C}$ ) per single diode system (cont'd)

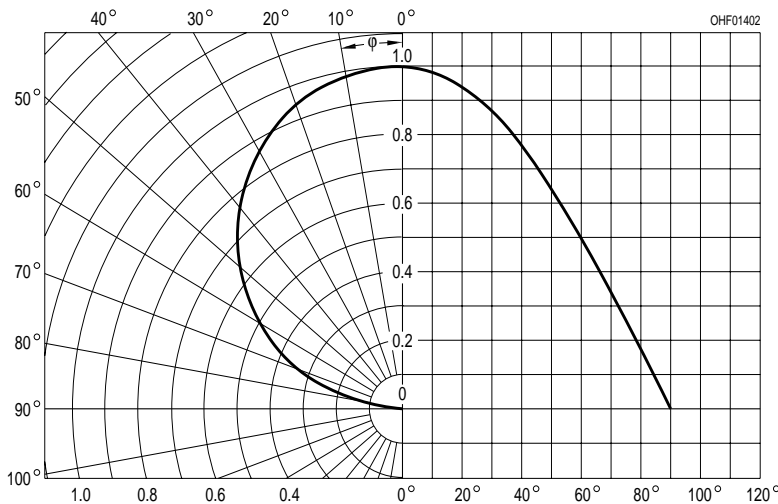
Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		BPX 48	BPX 48 F	
Halbwinkel Half angle	$\varphi$	$\pm 60$	$\pm 60$	Grad deg.
Dunkelstrom, $V_R = 10\text{ V}$ Dark current	$I_R$	10 ( $\leq 100$ )	10 ( $\leq 100$ )	nA
Spektrale Fotoempfindlichkeit Spectral sensitivity				
$\lambda = 850\text{ nm}$	$S_\lambda$	0.55	–	A/W
$\lambda = 950\text{ nm}$	$S_\lambda$	–	0.65	
Max. Abweichung der Fotoempfindlichkeit der Systeme vom Mittelwert Max. deviation of the system spectral sensitivity from the average	$\Delta S$	$\pm 5$	$\pm 5$	%
Quantenausbeute Quantum yield				<u>Electrons</u> Photon
$\lambda = 850\text{ nm}$	$\eta$	0.8	–	
$\lambda = 950\text{ nm}$	$\eta$	–	0.95	
Leerlaufspannung Open-circuit voltage				
$E_v = 1000\text{ lx}$ , Normlicht/standard light A, $T = 2856\text{ K}$	$V_O$	330 ( $\geq 280$ )	–	mV
$E_e = 0.5\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$V_O$	–	300 ( $\geq 280$ )	mV
Kurzschlußstrom Short-circuit current				
$E_v = 1000\text{ lx}$ , Normlicht/standard light A, $T = 2856\text{ K}$	$I_{SC}$	24	–	$\mu\text{A}$
$E_e = 0.5\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$I_{SC}$	–	7	$\mu\text{A}$
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent	$t_r, t_f$	500	500	ns
$R_L = 1\text{ k}\Omega$ ; $V_R = 5\text{ V}$ ; $\lambda = 850\text{ nm}$ ; $I_p = 20\text{ }\mu\text{A}$				
Durchlaßspannung, $I_F = 40\text{ mA}$ , $E = 0$ Forward voltage	$V_F$	1.3	1.3	V
Kapazität, $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$ Capacitance	$C_0$	25	25	pF
Temperaturkoeffizient von $V_O$ Temperature coefficient of $V_O$	$TC_V$	– 2.6	– 2.6	mV/K

**Kennwerte** ( $T_A = 25\text{ °C}$ ) für jede Einzeldiode  
**Characteristics** ( $T_A = 25\text{ °C}$ ) per single diode system (cont'd)

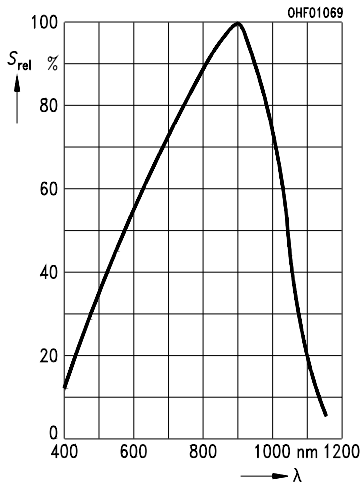
Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		BPX 48	BPX 48 F	
Temperaturkoeffizient von $I_{SC}$ Temperature coefficient of $I_{SC}$ Normlicht/standard light A $\lambda = 950\text{ nm}$	$TC_1$ $TC_1$	0.18 –	– 0.2	%/K %/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 10\text{ V}, \lambda = 950\text{ nm}$	$NEP$	$1.0 \times 10^{-13}$	$1.0 \times 10^{-13}$	$\frac{W}{\sqrt{Hz}}$
Nachweisgrenze, $V_R = 10\text{ V}, \lambda = 950\text{ nm}$ Detection limit	$D^*$	$1.2 \times 10^{12}$	$1.2 \times 10^{12}$	$\frac{cm \times \sqrt{Hz}}{W}$

**Directional Characteristics**

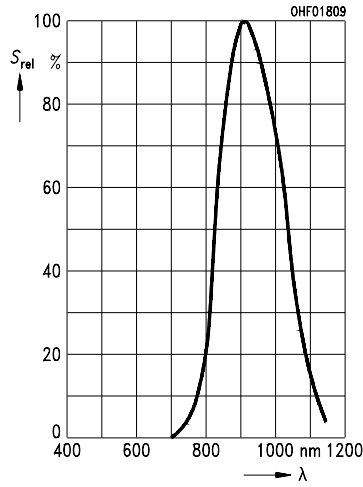
$S_{rel} = f(\varphi)$



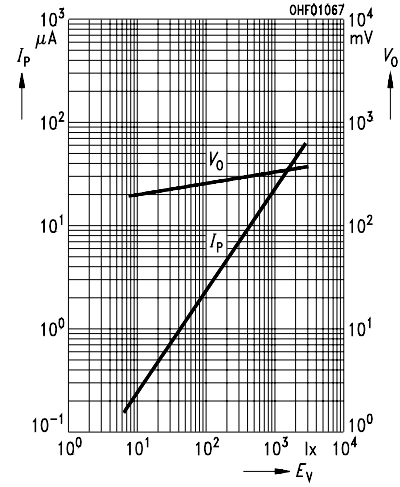
**Relative Spectral Sensitivity**  
BPX 48  $S_{rel} = f(\lambda)$



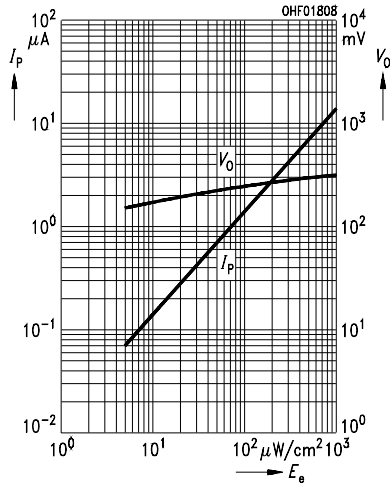
**Relative Spectral Sensitivity**  
BPX 48 F  $S_{rel} = f(\lambda)$



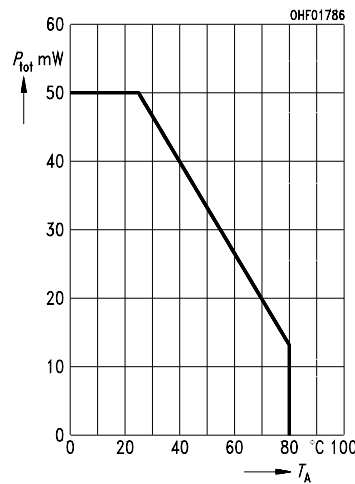
**Photocurrent  $I_P = f(E_V)$ ,  $V_R = 5 V$**   
**Open-Circuit-Voltage  $V_O = f(E_V)$**   
BPX 48



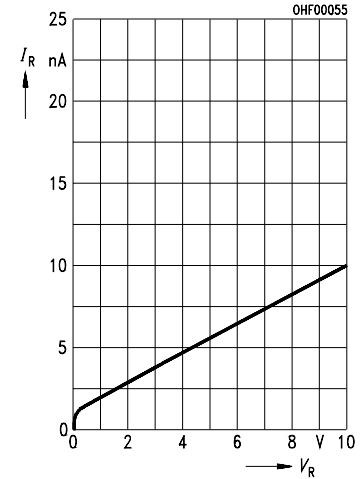
**Photocurrent  $I_P = f(E_e)$ ,  $V_R = 5 V$**   
**Open-Circuit-Voltage  $V_O = f(E_e)$**   
BPX 48 F



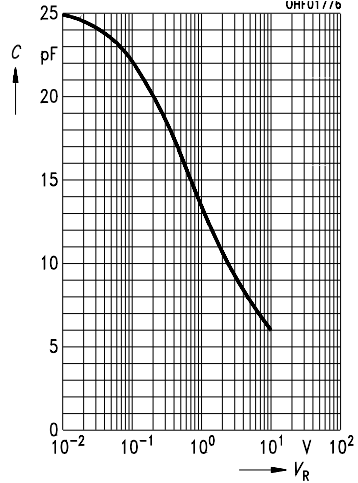
**Total Power Dissipation**  
 $P_{tot} = f(T_A)$



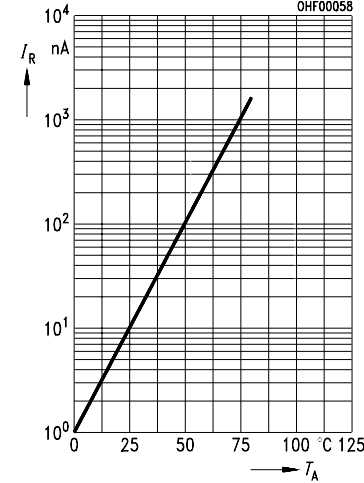
**Dark Current**  
 $I_R = f(V_R), E = 0$



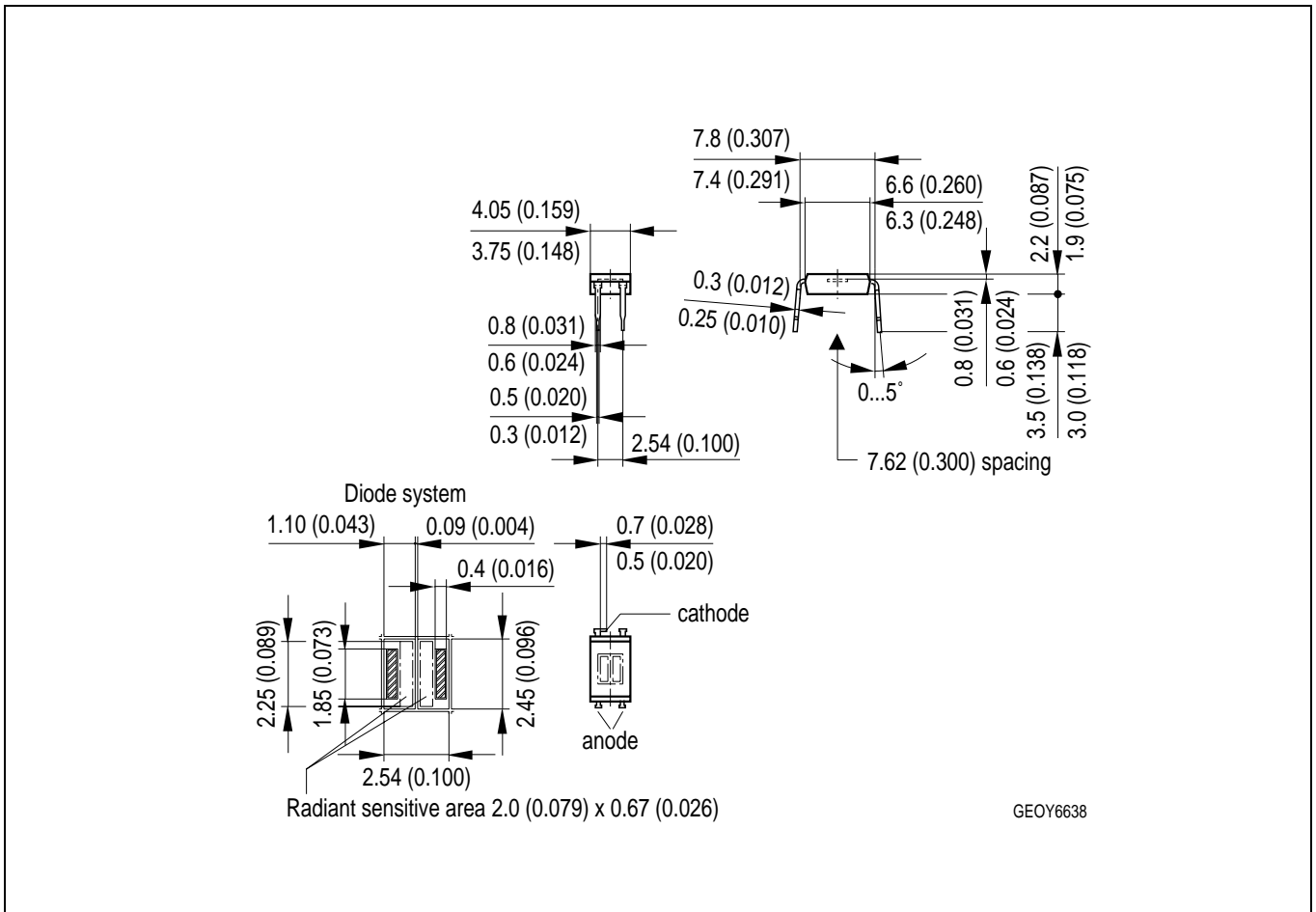
**Capacitance**  
 $C = f(V_R), f = 1 MHz, E = 0$



**Dark Current**  
 $I_R = f(T_A), V_R = 10 V$



**Maßzeichnung  
Package Outlines**



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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